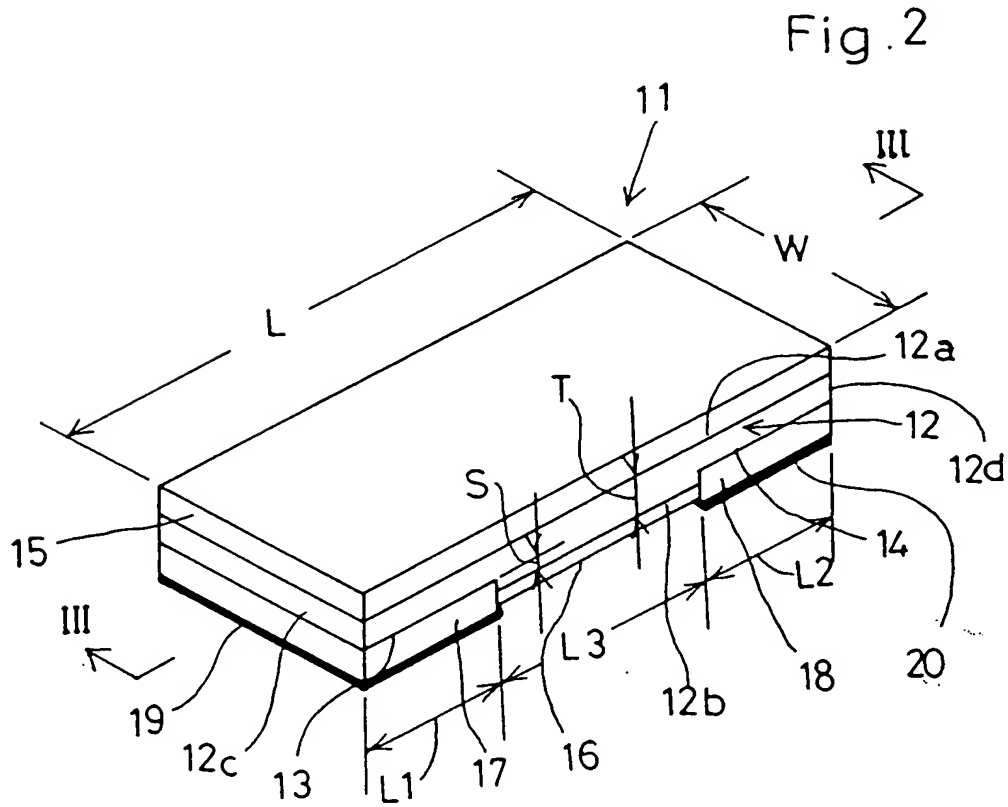
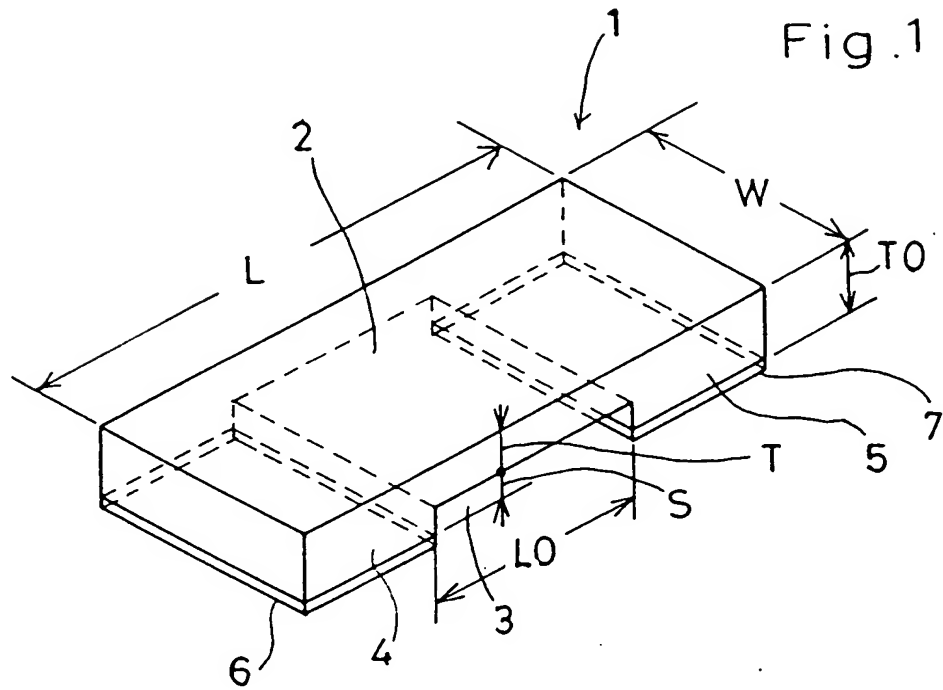
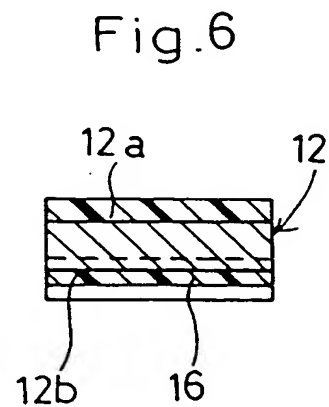
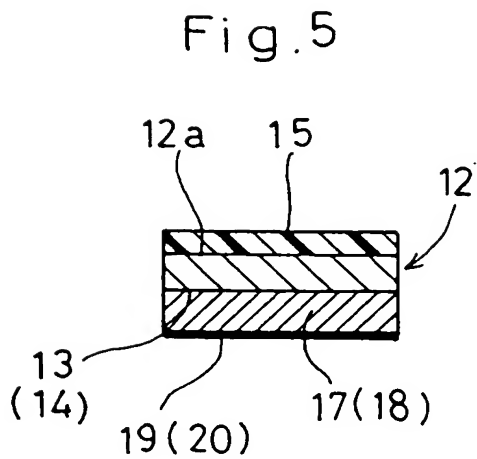
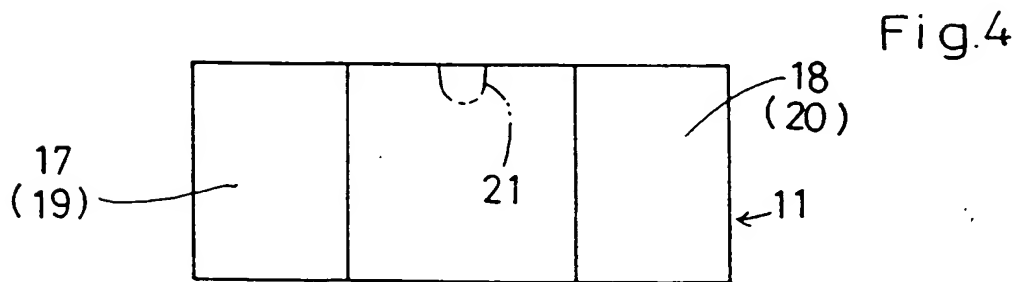
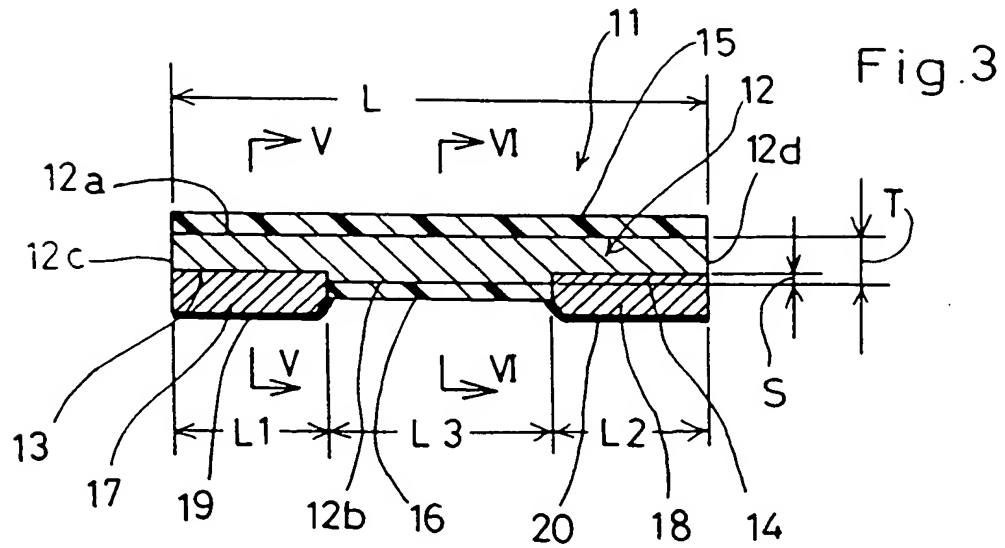
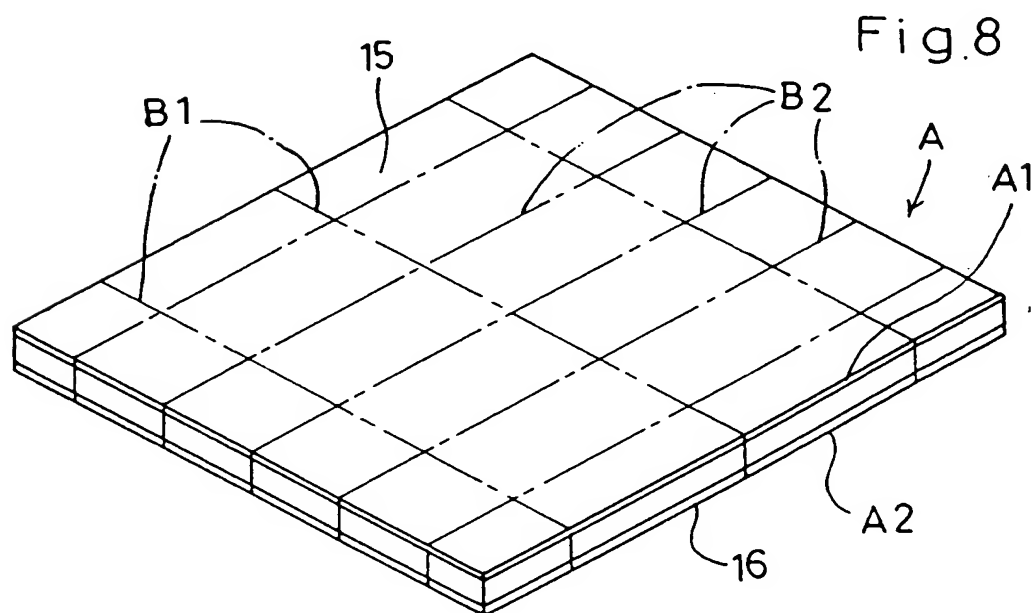
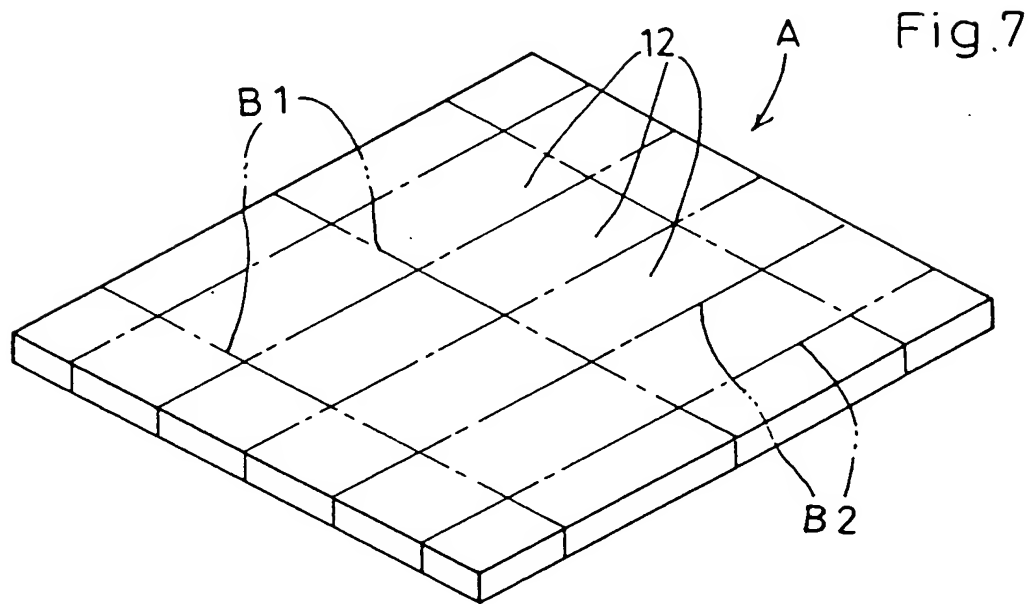


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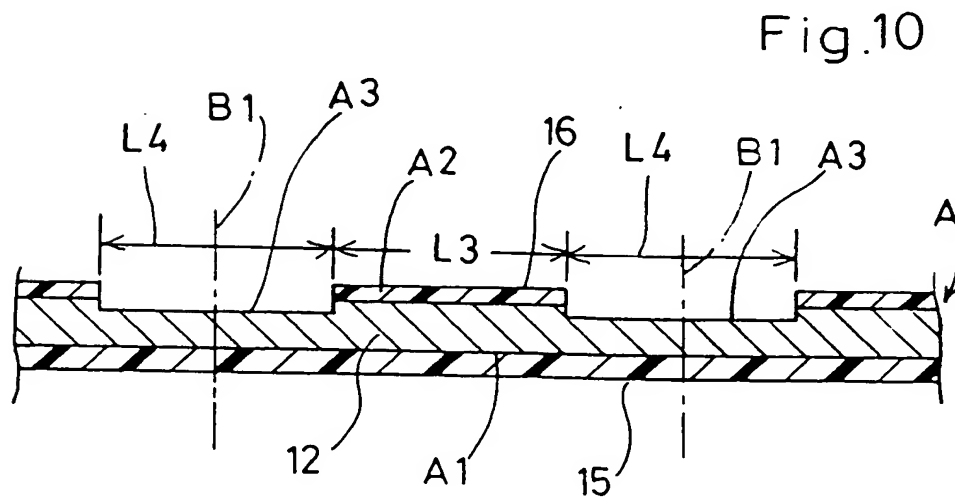
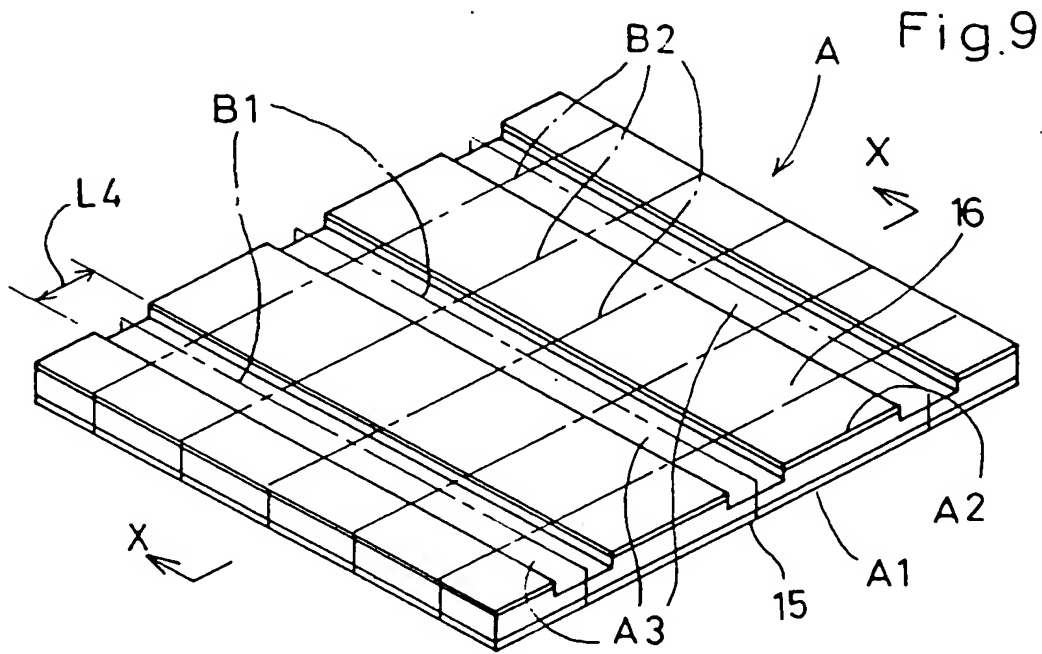


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Fig.11

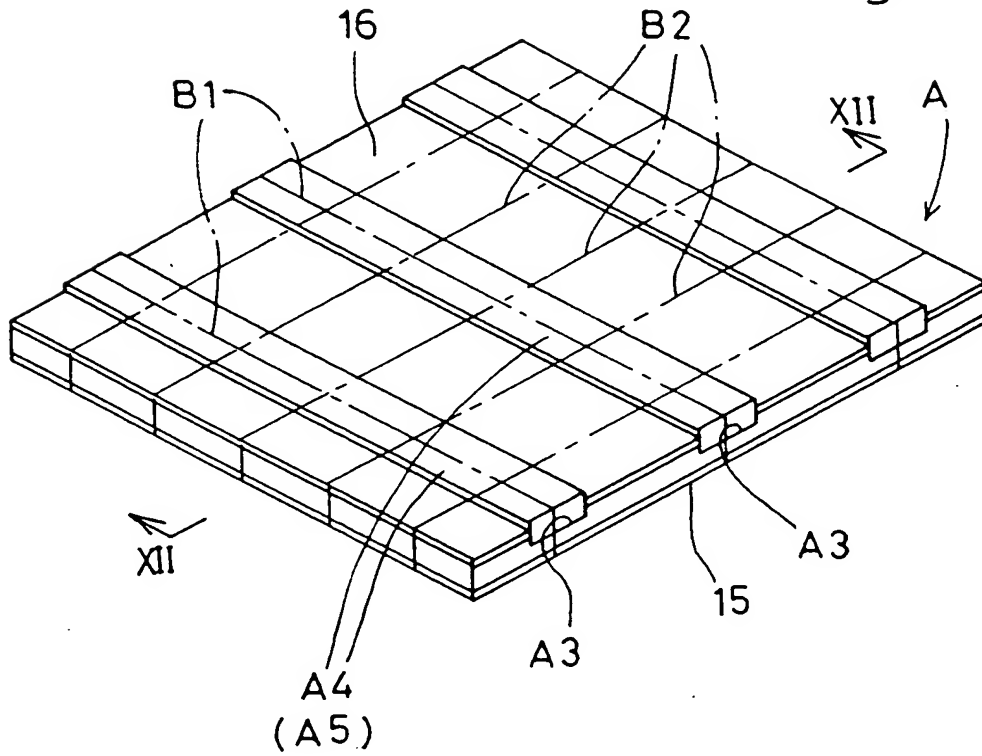
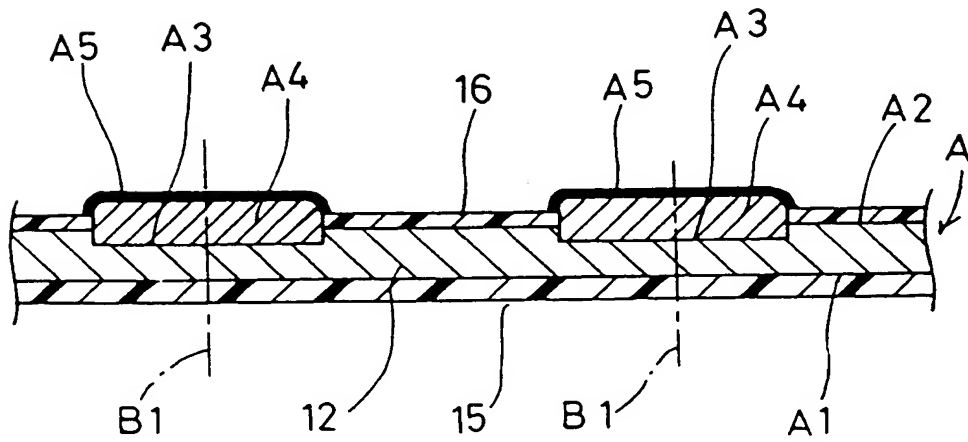


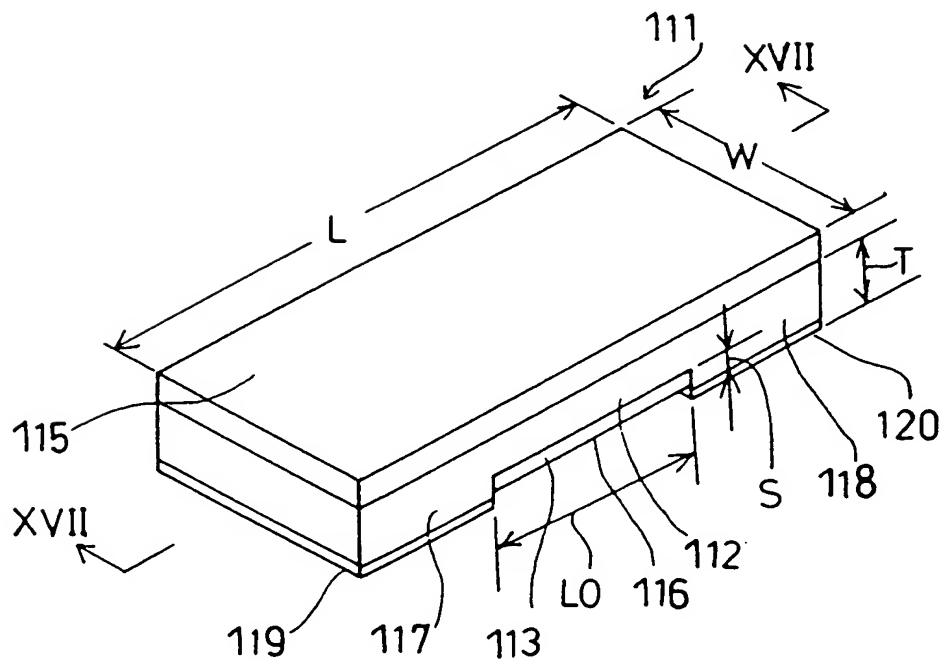
Fig.12



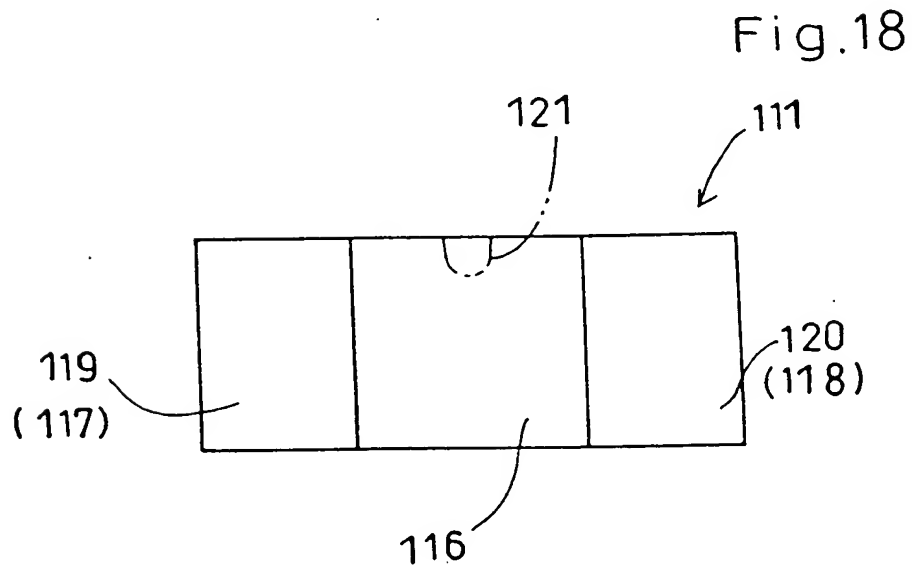
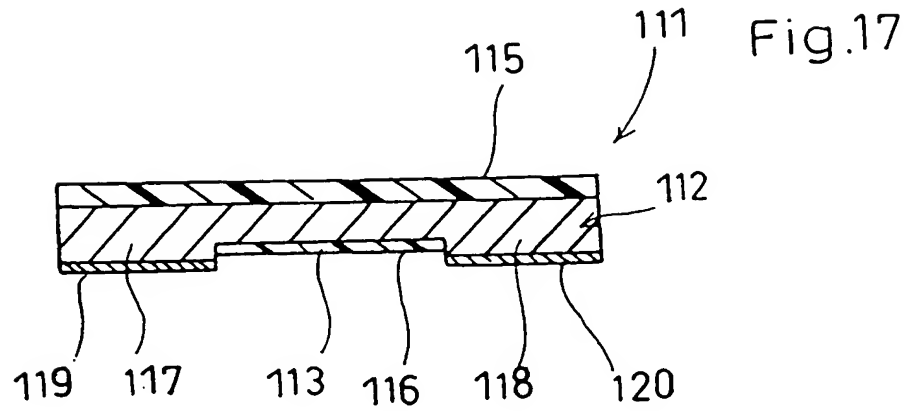
A cross-sectional diagram of a semiconductor device. It shows a substrate with several layers. A central layer is labeled 16, with a width indicated by L3. Above this layer are two regions labeled B1. The top surface has several rectangular features labeled A3'', A3', and A2. Below the central layer 16, there are regions labeled 11' and 15. On the right side, there is a region labeled A1. The entire structure is bounded by a vertical line on the left and a curved arrow labeled A on the right.

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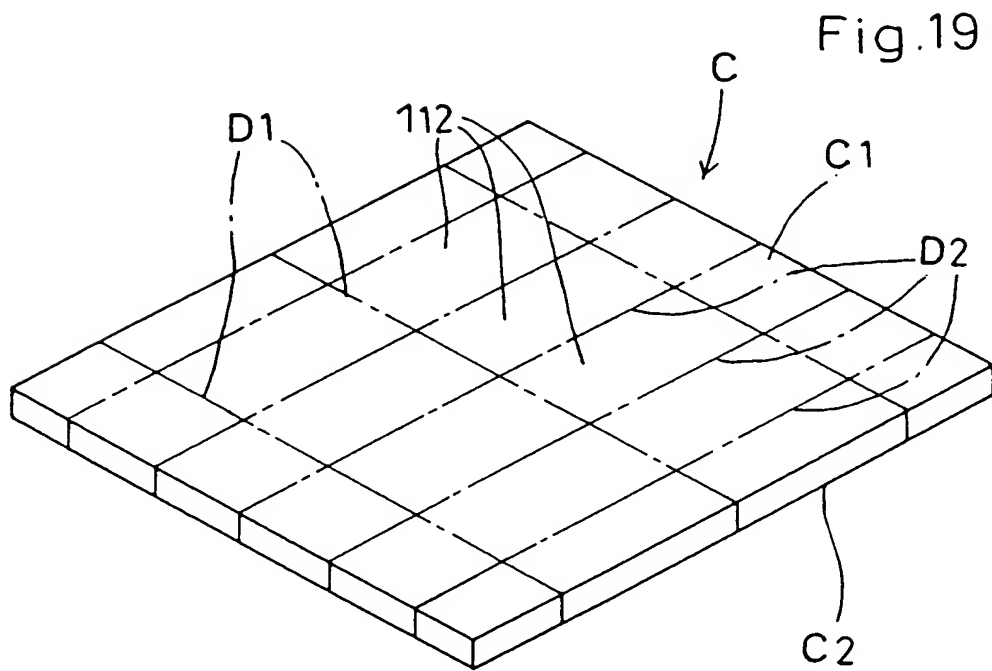
Fig. 16



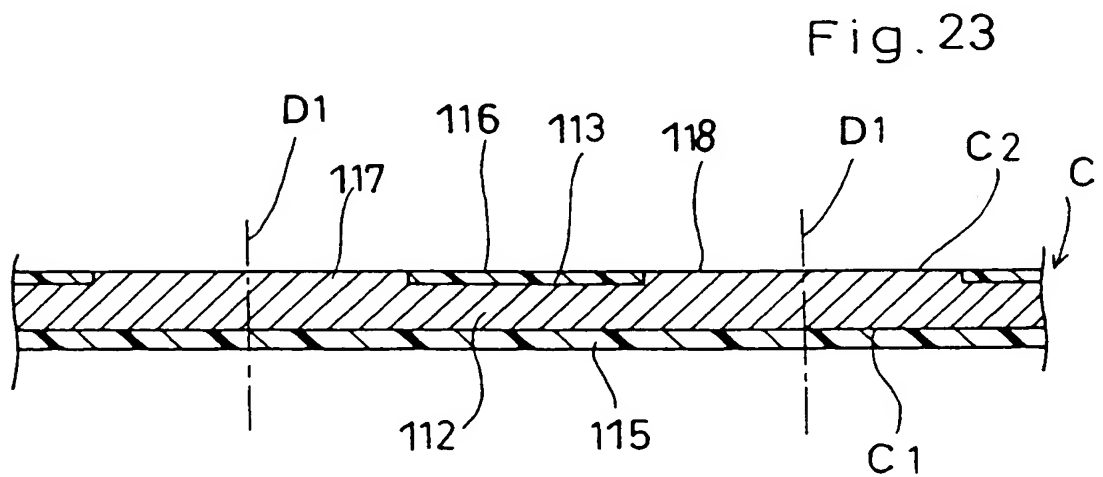
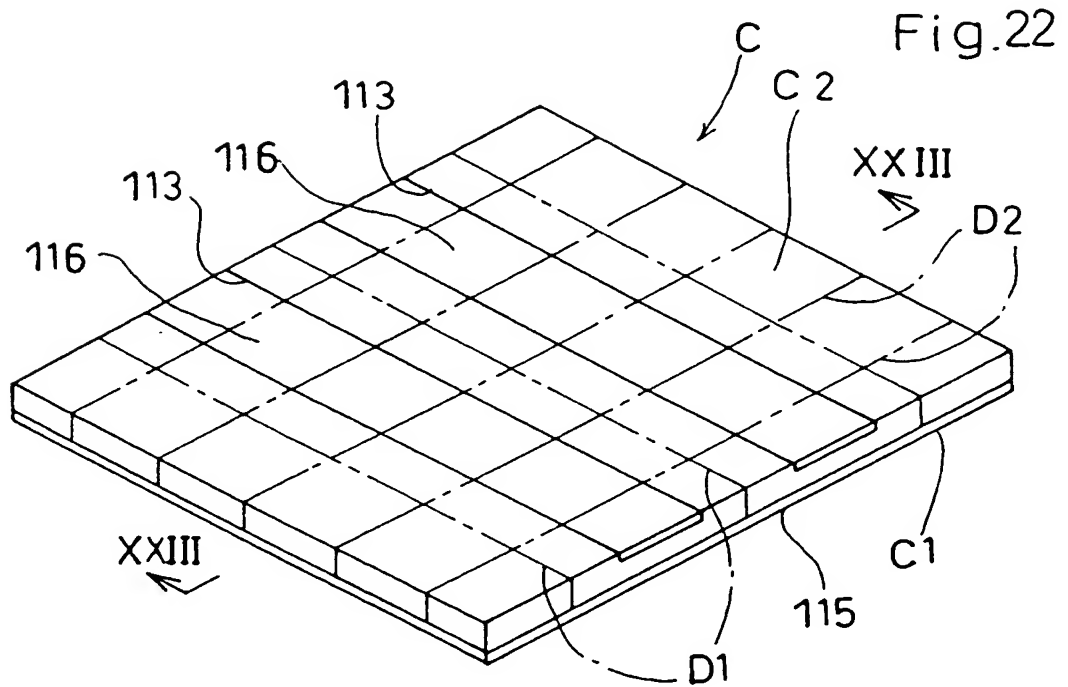
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